

NVMFD5C668NL

MOSFET – Power, Dual N-Channel

60 V, 6.5 mΩ, 68 A

Features

- Small Footprint (5x6 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- NVMFD5C668NLWF – Wettable Flank Option for Enhanced Optical Inspection
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V _{DSS}	60	V
Gate-to-Source Voltage			V _{GS}	±20	V
Continuous Drain Current R _{θJC} (Notes 1, 2, 3)	Steady State	T _C = 25°C	I _D	68	A
		T _C = 100°C		48	
Power Dissipation R _{θJC} (Notes 1, 2)		T _C = 25°C	P _D	57.5	W
		T _C = 100°C		29	
Continuous Drain Current R _{θJA} (Notes 1, 2, 3)	Steady State	T _A = 25°C	I _D	15.5	A
		T _A = 100°C		11	
Power Dissipation R _{θJA} (Notes 1 & 2)		T _A = 25°C	P _D	3.0	W
		T _A = 100°C		1.5	
Pulsed Drain Current	T _A = 25°C, t _p = 10 μs		I _{DM}	454	A
Operating Junction and Storage Temperature			T _J , T _{stg}	–55 to +175	°C
Source Current (Body Diode)			I _S	48	A
Single Pulse Drain-to-Source Avalanche Energy (T _J = 25°C, I _{L(pk)} = 3.22 A)			E _{AS}	205	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T _L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case – Steady State	$R_{\theta JC}$	2.6	$^\circ\text{C/W}$
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	50.26	

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 650 mm², 2 oz. Cu pad.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

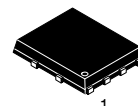
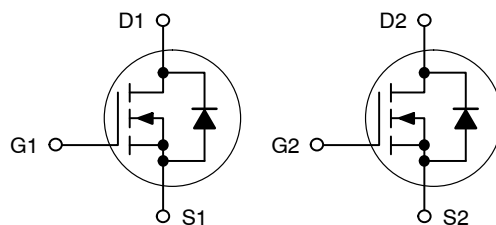


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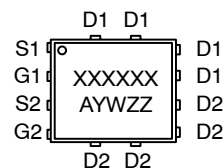
$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
60 V	6.5 mΩ @ 10 V	68 A
	9.2 mΩ @ 4.5 V	

Dual N-Channel



DFN8 5x6
(SO8FL)
CASE 506BT

MARKING DIAGRAM



XXXXXX = 5C668L (NVMFD5C668NL) or
668LWF (NVMFD5C668NLWF)

A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

NVMFD5C668NL

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	60			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			28		mV/ $^\circ\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 60\text{ V}$	$T_J = 25^\circ\text{C}$		10	μA
			$T_J = 125^\circ\text{C}$		250	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = 20\text{ V}$			100	nA

ON CHARACTERISTICS (Note 4)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 50\text{ }\mu\text{A}$	1.2		2.0	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			-5.3		mV/ $^\circ\text{C}$
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 20\text{ A}$		5.4	6.5	$\text{m}\Omega$
		$V_{GS} = 4.5\text{ V}, I_D = 20\text{ A}$		7.4	9.2	
Forward Transconductance	g_{FS}	$V_{DS} = 15\text{ V}, I_D = 20\text{ A}$		61		S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 25\text{ V}$		1440		pF
Output Capacitance	C_{OSS}			800		
Reverse Transfer Capacitance	C_{RSS}			14		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 48\text{ V}, I_D = 20\text{ A}$		9.8		nC
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{ V}, V_{DS} = 48\text{ V}, I_D = 20\text{ A}$		21.3		
Threshold Gate Charge	$Q_{G(TH)}$	$V_{GS} = 10\text{ V}, V_{DS} = 48\text{ V}, I_D = 20\text{ A}$		2.5		
Gate-to-Source Charge	Q_{GS}			4.3		
Gate-to-Drain Charge	Q_{GD}			2.1		
Plateau Voltage	V_{GP}			2.9		V

SWITCHING CHARACTERISTICS (Note 5)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 10\text{ V}, V_{DS} = 48\text{ V}, I_D = 20\text{ A}, R_G = 1.0\text{ }\Omega$		10		ns
Rise Time	t_r			22		
Turn-Off Delay Time	$t_{d(OFF)}$			40		
Fall Time	t_f			7.0		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V},$ $I_S = 20\text{ A}$	$T_J = 25^{\circ}\text{C}$		0.85	1.2	V
			$T_J = 125^{\circ}\text{C}$		0.73		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s},$ $I_S = 20\text{ A}$			42		ns
Charge Time	t_a				20		
Discharge Time	t_b				22		
Reverse Recovery Charge	Q_{RR}				32		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

5. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

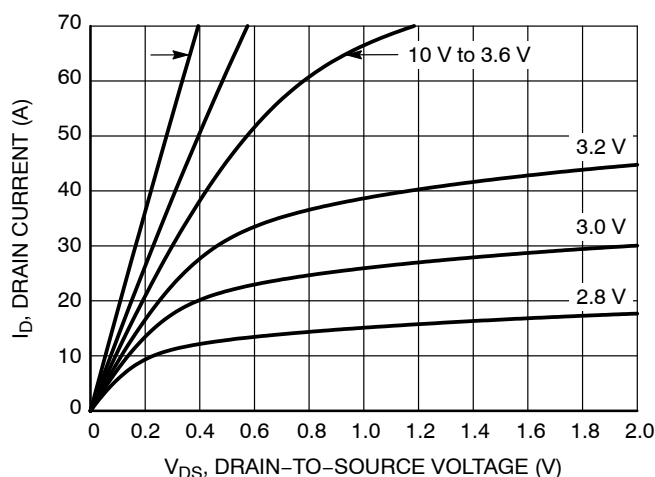


Figure 1. On-Region Characteristics

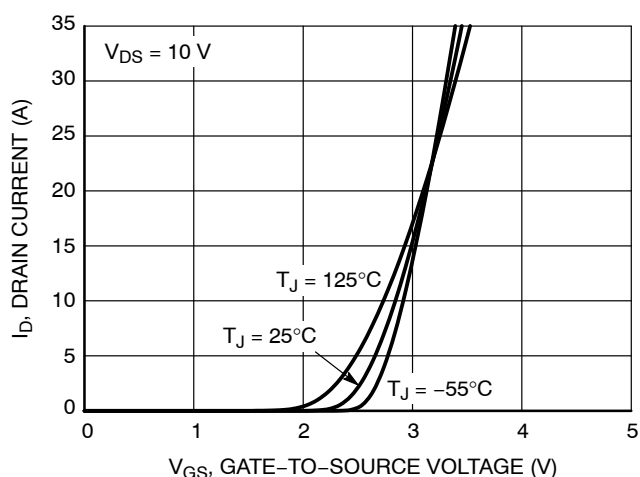


Figure 2. Transfer Characteristics

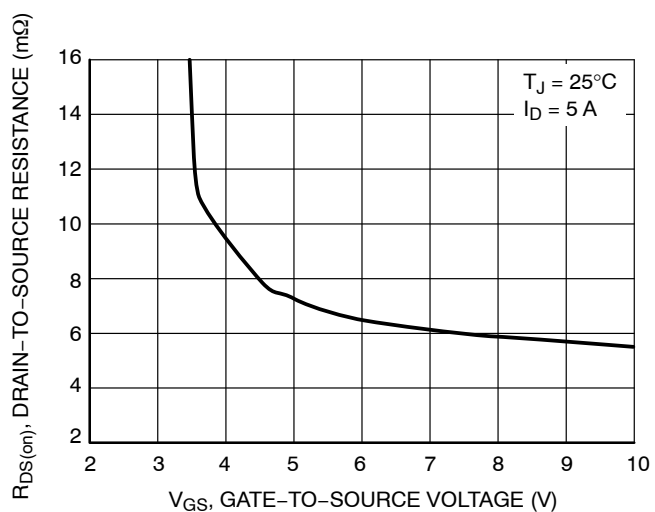


Figure 3. On-Resistance vs. Gate-to-Source Voltage

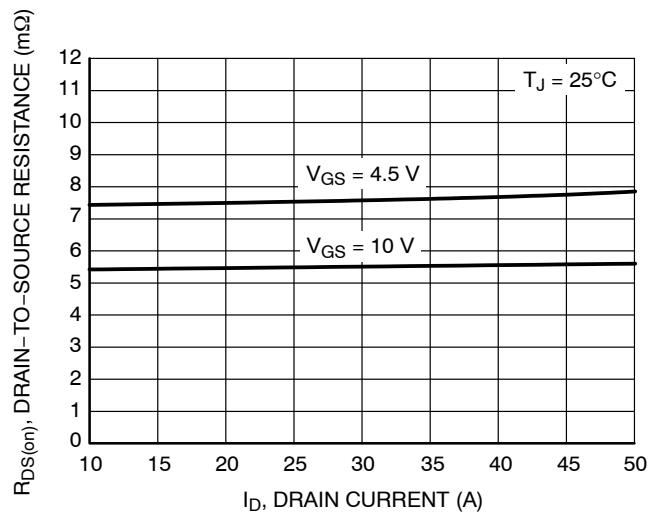


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

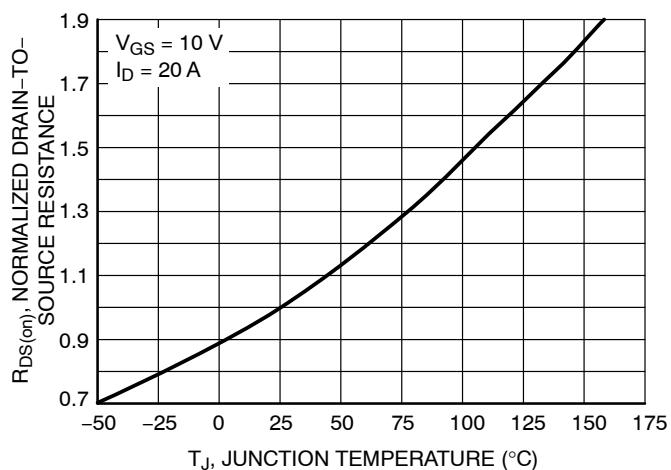


Figure 5. On-Resistance Variation with Temperature

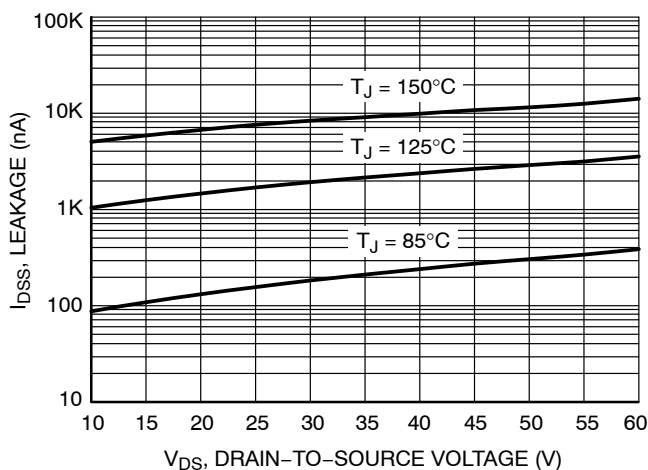


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

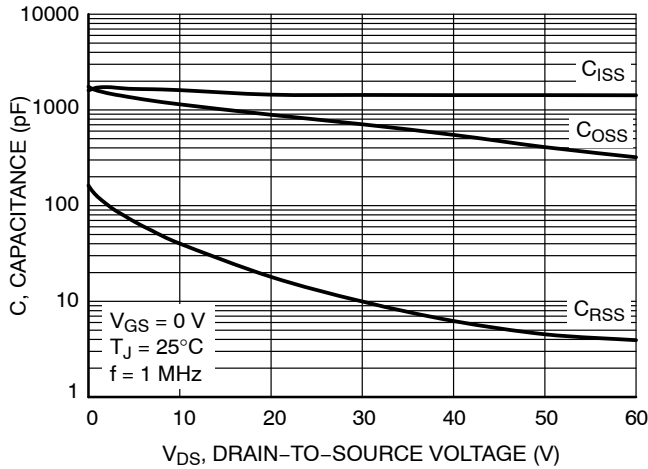


Figure 7. Capacitance Variation

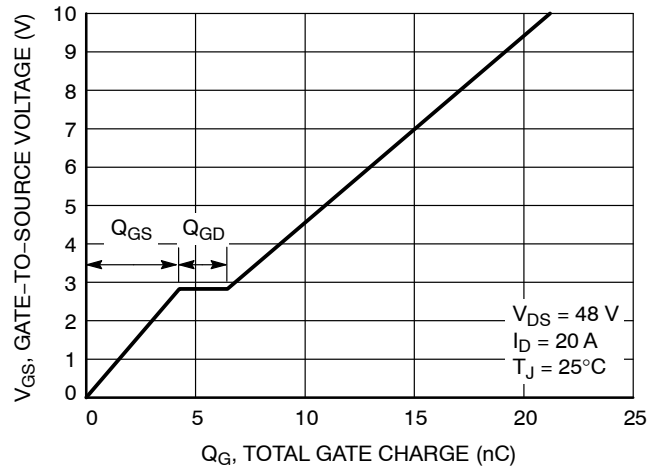


Figure 8. Gate-to-Source Voltage vs. Total Charge

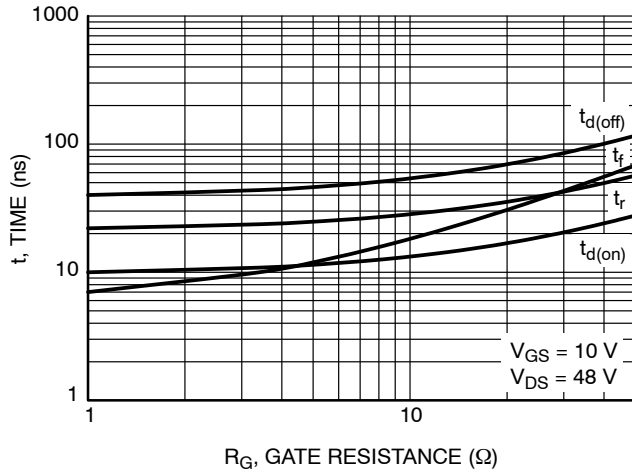


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

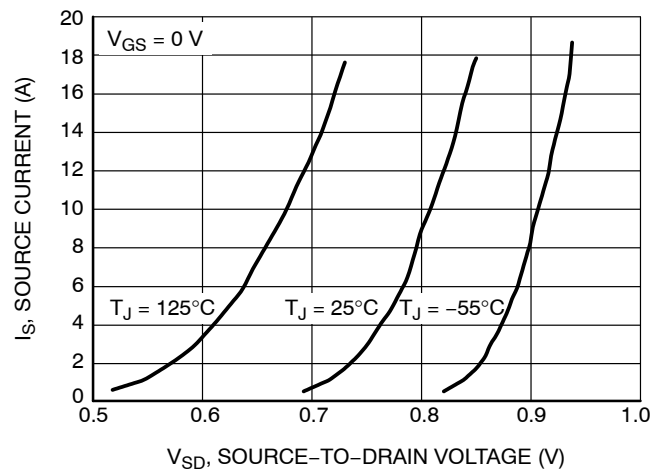


Figure 10. Diode Forward Voltage vs. Current

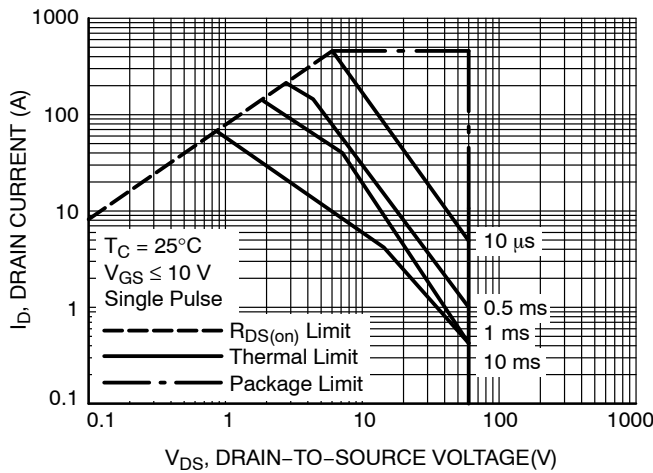


Figure 11. Maximum Rated Forward Biased Safe Operating Area

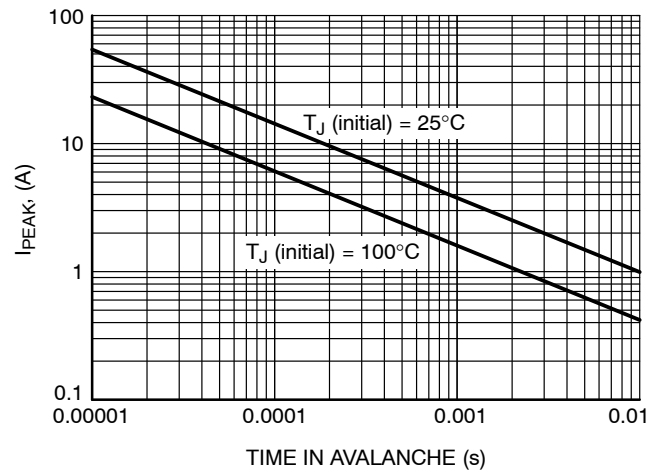


Figure 12. I_{PEAK} vs. Time in Avalanche

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TYPICAL CHARACTERISTICS

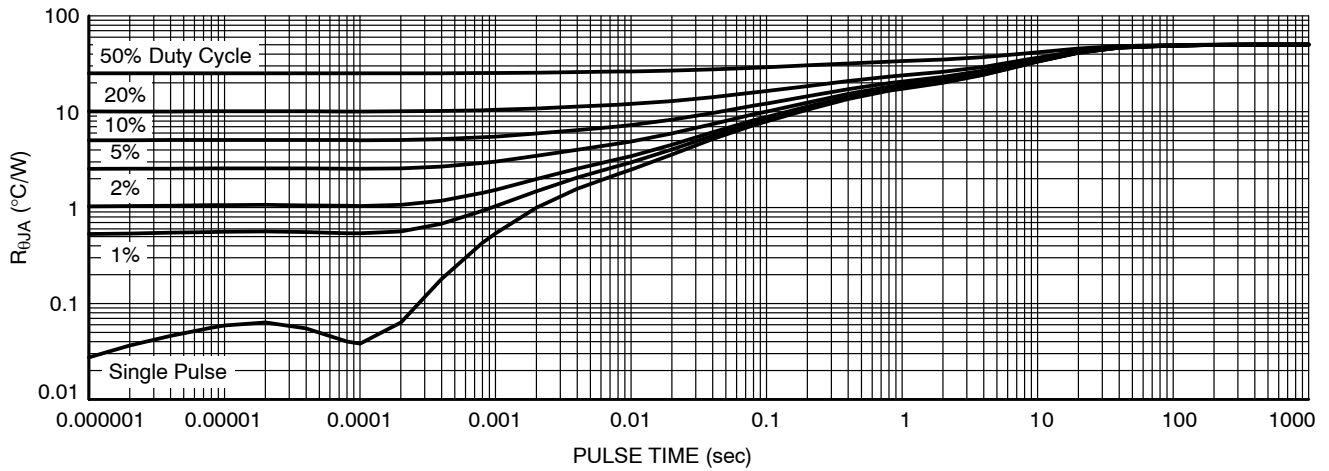


Figure 13. Thermal Characteristics

DEVICE ORDERING INFORMATION

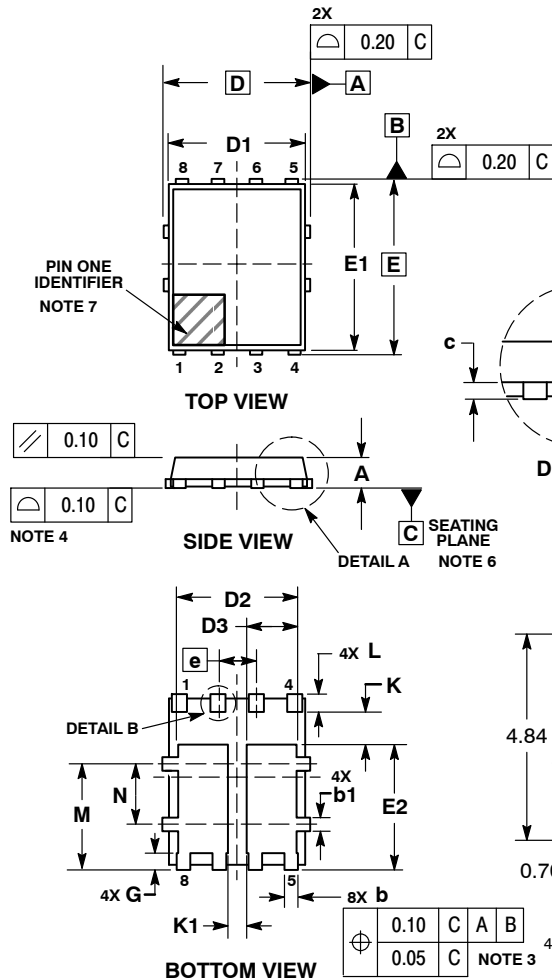
Device	Marking	Package	Shipping [†]
NVMFD5C668NLT1G	5C668L	DFN8 (Pb-Free)	1500 / Tape & Reel
NVMFD5C668NLWFT1G	668LWF	DFN8 (Pb-Free, Wettable Flanks)	1500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NVMFD5C668NL

PACKAGE DIMENSIONS

DFN8 5x6, 1.27P Dual Flag (SO8FL-Dual) CASE 506BT ISSUE E



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 MM FROM THE TERMINAL TIP.
4. PROFILE TOLERANCE APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.
5. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
6. SEATING PLANE IS DEFINED BY THE TERMINALS. A1 IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.
7. A VISUAL INDICATOR FOR PIN 1 MUST BE LOCATED IN THIS AREA.

DIM	MILLIMETERS		
	MIN	MAX	MAX
A	0.90	---	1.10
A1	---	---	0.05
b	0.33	0.42	0.51
b1	0.33	0.42	0.51
c	0.20	---	0.33
D	5.15 BSC		
D1	4.70	4.90	5.10
D2	3.90	4.10	4.30
D3	1.50	1.70	1.90
E	6.15 BSC		
E1	5.70	5.90	6.10
E2	3.90	4.15	4.40
e	1.27 BSC		
G	0.45	0.55	0.65
h	---	---	12 °
K	0.51	---	---
K1	0.56	---	---
L	0.48	0.61	0.71
M	3.25	3.50	3.75
N	1.80	2.00	2.20

SOLDERING FOOTPRINT*

